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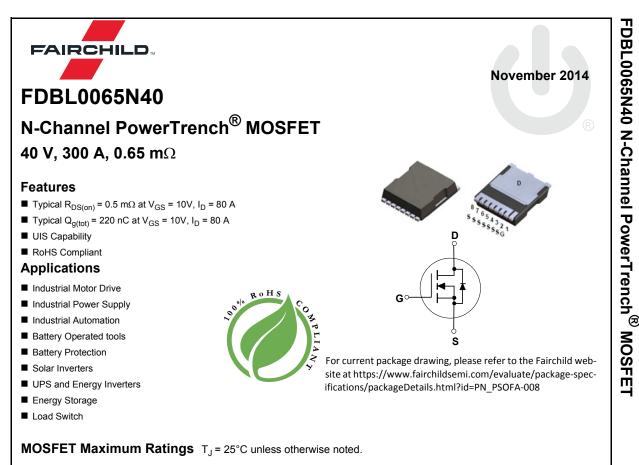


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| Symbol                            | Parameter   |                       | Ratings      | Units |  |
|-----------------------------------|---|-----------------------|--------------|-------|--|
| V <sub>DSS</sub>                  | Drain-to-Source Voltage                                   |                       | 40           | V     |  |
| V <sub>GS</sub>                   | Gate-to-Source Voltage                                    |                       | ±20          | V     |  |
| I <sub>D</sub>                    | Drain Current - Continuous (V <sub>GS</sub> =10) (Note 1) | T <sub>C</sub> =25°C  | 300          | Α     |  |
|                                   | Pulsed Drain Current                                      | T <sub>C</sub> = 25°C | See Figure 4 |       |  |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy                             | (Note 2)              | 1064         | mJ    |  |
|                                   | Power Dissipation   |                       | 429          | W     |  |
| P <sub>D</sub>                    | Derate Above 25°C   |                       | 2.86         | W/ºC  |  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature                         |                       | -55 to + 175 | °C    |  |
| R <sub>0JC</sub>                  | Thermal Resistance, Junction to Case                      |                       | 0.35         | °C/W  |  |
| $R_{\theta JA}$                   | Maximum Thermal Resistance, Junction to Ambient           | (Note 3)              | 43           | °C/W  |  |

Notes:

1: Current is limited by bondwire configuration.

2: Starting  $T_J = 25^{\circ}$ C, L = 0.3mH,  $I_{AS} = 84A$ ,  $V_{DD} = 40V$  during inductor charging and  $V_{DD} = 0V$  during time in avalanche.

3: R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>0JC</sub> is guaranteed by design, while R<sub>0JA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

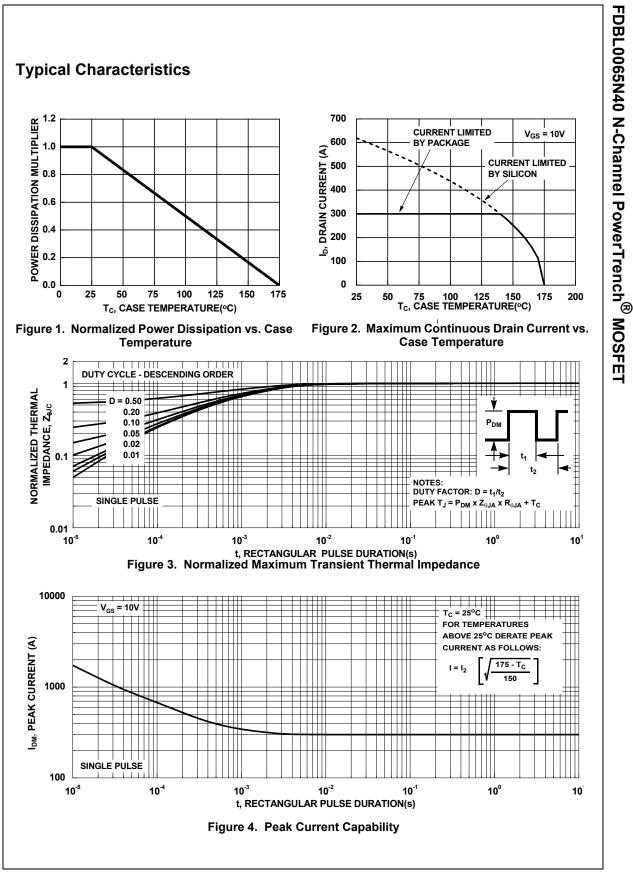
#### Package Marking and Ordering Information

| Device Marking | Device      | Package |   |   |   |
|----------------|-------------|---------|---|---|---|
| FDBL0065N40    | FDBL0065N40 | MO-299A | - | - | - |

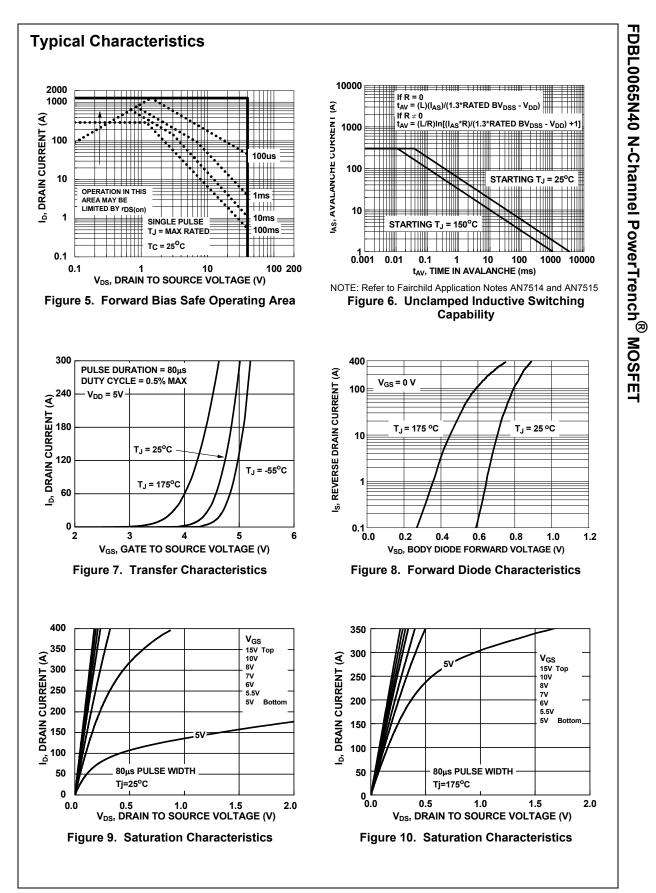
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| Symbol                     | Parameter                         | Test C   | onditions                                  | Min. | Тур.                                    | Max. | Units    |
|----------------------------|-----------------------------------|--|--|------|---|------|----------|
|                            | racteristics                      |  |  |      | ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,, | -    |          |
| B <sub>VDSS</sub>          | Drain-to-Source Breakdown Voltage | I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V             |  | 40   | -                                       | -    | V        |
|                            |                                   | V <sub>DS</sub> =40V, T                                  |  | -    | -                                       | 1    | μA       |
| IDSS                       | Drain-to-Source Leakage Current   | V <sub>GS</sub> = 0V T                                   | <sub>J</sub> = 175 <sup>o</sup> C (Note 4) | -    | -                                       | 1    | mA       |
| I <sub>GSS</sub>           | Gate-to-Source Leakage Current    | $V_{GS} = \pm 20V$                                       |  | -    | -                                       | ±100 | nA       |
| On Cha                     | racteristics                      |  |  |      |   |      |          |
| V <sub>GS(th)</sub>        | Gate to Source Threshold Voltage  | $V_{GS} = V_{DS}, I_D =$                                 | = 250μA                                    | 2.0  | 3.0                                     | 4.0  | V        |
| D                          | Drain to Source On Resistance     | D /  | J = 25°C                                   | -    | 0.50                                    | 0.65 | mΩ       |
| R <sub>DS(on)</sub>        |                                   | V <sub>GS</sub> = 10V T                                  | <sub>J</sub> = 175 <sup>o</sup> C (Note 4) | -    | 0.86                                    | 1.10 | mΩ       |
| Dynami<br>C <sub>iss</sub> | c Characteristics                 |  |  |      | 15900                                   | -    | рF       |
| C <sub>oss</sub>           | Output Capacitance                | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,<br>f = 1MHz |  | -    | 4025                                    | -    | p.<br>pF |
| C <sub>rss</sub>           | Reverse Transfer Capacitance      |  |  | -    | 604                                     | -    | pF       |
| R <sub>a</sub>             | Gate Resistance                   |  |  | -    | 2.6                                     | -    | Ω        |
| Q <sub>g(ToT)</sub>        | Total Gate Charge at 10V          | V <sub>GS</sub> = 0 to 10V                               | V <sub>DD</sub> = 20V                      | -    | 220                                     | 296  | nC       |
| $Q_{g(th)}$                | Threshold Gate Charge             | $V_{GS} = 0$ to 2V                                       | $I_{\rm D} = 80A$                          | -    | 29                                      | 39   | nC       |
| Q <sub>gs</sub>            | Gate to Source Gate Charge        |  |  | -    | 73                                      | -    | nC       |
| Q <sub>gd</sub>            | Gate to Drain "Miller" Charge     |  |  | -    | 41                                      | -    | nC       |
| Switchi                    | ng Characteristics                |  |  |      | -                                       | 221  | ns       |
| t <sub>d(on)</sub>         | Turn-On Delay                     |  |  | -    | 54                                      | -    | ns       |
| r                          | Rise Time                         | V <sub>DD</sub> = 20V, I <sub>D</sub> =                  | = 80A,                                     | -    | 82                                      | -    | ns       |
| t <sub>d(off)</sub>        | Turn-Off Delay                    | V <sub>GS</sub> = 10V, R <sub>G</sub>                    |  | -    | 106                                     | -    | ns       |
| t <sub>f</sub>             | Fall Time                         |  |  | -    | 52                                      | -    | ns       |
| t <sub>off</sub>           | Turn-Off Time                     |  |  | -    | -                                       | 215  | ns       |
| Drain-S                    | ource Diode Characteristics       |  |  |      |   |      |          |
| V <sub>SD</sub>            | Source to Drain Diode Voltage     | I <sub>SD</sub> =80A, V <sub>GS</sub> = 0V               |  | -    | -                                       | 1.25 | V        |
| - 20                       | -                                 | I <sub>SD</sub> = 40A, V <sub>GS</sub>                   |  | -    | -                                       | 1.2  | V        |
| t <sub>rr</sub>            | Reverse Recovery Time             | $I_{F} = 80A, dI_{SD}/dt = 100A/\mu s,$                  |  | -    | 119                                     | 133  | ns       |
| Q <sub>rr</sub>            | Reverse Recovery Charge           |  | V <sub>DD</sub> =32V                       |      | 228                                     | 274  | nC       |

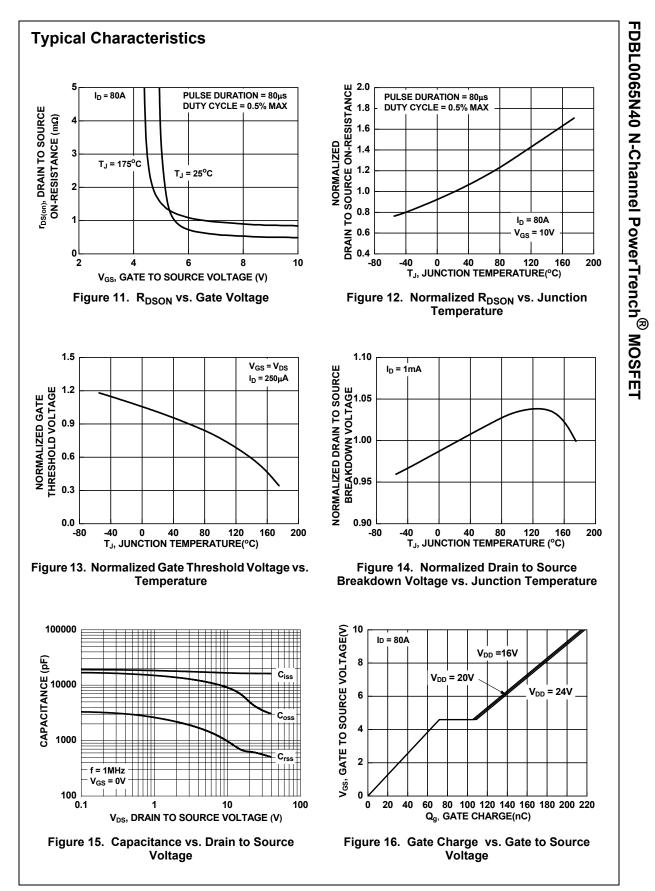
4: The maximum value is specified by design at  $T_J$  = 175°C. Product is not tested to this condition in production.



FDBL0065N40 Rev.C3



FDBL0065N40 Rev.C3



FDBL0065N40 Rev.C3



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